Qing-Tai Zhao

List of Publications by Year
in descending order

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169 papers	2,165 citations	279701 23 h-index	302012 39 g-index
171 all docs	171 docs citations	171 times ranked	1604 citing authors

#	Article	IF	Citations
1	Steep Switching Si Nanowire p-FETs With Dopant Segregated Silicide Source/Drain at Cryogenic Temperature. IEEE Electron Device Letters, 2022, 43, 1187-1190.	2.2	7
2	Epitaxial GeSn/Ge Vertical Nanowires for p-Type Field-Effect Transistors with Enhanced Performance. ACS Applied Nano Materials, 2021, 4, 94-101.	2.4	12
3	Artificial Synapses Based on Ferroelectric Schottky Barrier Field-Effect Transistors for Neuromorphic Applications. ACS Applied Materials & Interfaces, 2021, 13, 32005-32012.	4.0	43
4	4-Terminal Ferroelectric Schottky Barrier Field Effect Transistors as Artificial Synapses. , 2021, , .		2
5	Diameter Scaling of Vertical Ge Gate- All-Around Nanowire pMOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 2988-2994.	1.6	13
6	Vertical Ge Gate-All-Around Nanowire pMOSFETs With a Diameter Down to 20 nm. IEEE Electron Device Letters, 2020, 41, 533-536.	2.2	13
7	Impact of gate to source/drain alignment on the static and RF performance of junctionless Si nanowire n-MOSFETs. Solid-State Electronics, 2020, 169, 107817.	0.8	0
8	Phase evolution of ultra-thin Ni silicide films on CF4 plasma immersion ion implanted Si. Nanotechnology, 2020, 31, 205201.	1.3	2
9	2-D Physics-Based Compact DC Modeling of Double-Gate Tunnel-FETs. IEEE Transactions on Electron Devices, 2019, 66, 132-138.	1.6	29
10	A T-Shaped SOI Tunneling Field-Effect Transistor With Novel Operation Modes. IEEE Journal of the Electron Devices Society, 2019, 7, 1114-1118.	1.2	9
11	Impact of Gateâ€“Source Overlap on the Device/Circuit Analog Performance of Line TFETs. IEEE Transactions on Electron Devices, 2019, 66, 4081-4086.	1.6	24
12	Transient negative capacitance and charge trapping in FDSOI MOSFETs with ferroelectric HfYOX. Solid-State Electronics, 2019, 159, 71-76.	0.8	7
13	Strained Silicon Complementary TFET SRAM: Experimental Demonstration and Simulations. IEEE Journal of the Electron Devices Society, 2018, 6, 1033-1040.	1.2	29
14	Effect of hysteretic and non-hysteretic negative capacitance on tunnel FETs DC performance. Nanotechnology, 2018, 29, 095202.	1.3	32
15	Characteristics of Recessed-Gate TFETs With Line Tunneling. IEEE Transactions on Electron Devices, 2018, 65, 769-775.	1.6	22
16	A Novel Gate-Normal Tunneling Field-Effect Transistor With Dual-Metal Gate. IEEE Journal of the Electron Devices Society, 2018, 6, 1070-1076.	1.2	13
17	Subthreshold Behavior of Floating-Gate MOSFETs With Ferroelectric Capacitors. IEEE Transactions on Electron Devices, 2018, 65, 4641-4645.	1.6	10
18	Correlation of Bandgap Reduction with Inversion Response in (Si)GeSn/High-k/Metal Stacks. ACS Applied Materials & Interfaces, 2017, 9, 9102-9109.	4.0	7

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19	Benchmarking of Homojunction Strained-Si NW Tunnel FETs for Basic Analog Functions. IEEE Transactions on Electron Devices, 2017, 64, 1441-1448.	1.6	13
20	Experimental Investigation of ${C}$ â€“ ${V}$ Characteristics of Si Tunnel FETs. IEEE Electron Device Letters, 2017, 38, 818-821.	2.2	3
21	Ultrathin lateral unidirectional bipolar-type insulated-gate transistor as pH sensor. , 2017, , .		0
22	Experimental I â€“ V and C â€“ V Analysis of Schottky-Barrier Metal-Oxide-Semiconductor Field Effect Transistors with Epitaxial NiSi 2 Contacts and Dopant Segregation. Chinese Physics Letters, 2017, 34, 078501.	1.3	0
23	Static noise margin analysis of 8T TFET SRAM cells using a 2D compact model adapted to measurement data of fabricated TFET devices. , 2017, , .		2
24	Negative Capacitance as Performance Booster for Tunnel FETs and MOSFETs: An Experimental Study. IEEE Electron Device Letters, 2017, 38, 1485-1488.	2.2	62
25	Impact of Al addition on the formation of Ni germanosilicide layers under different temperature annealing *. Chinese Physics B, 2017, 26, 098503.	0.7	0
26	Analog and RF analysis of gate all around silicon nanowire MOSFETs. , 2017, , .		5
27	Experimental examination of tunneling paths in SiGe/Si gate-normal tunneling field-effect transistors. Applied Physics Letters, 2017, 111, .	1.5	5
28	Schottky barrier tuning via dopant segregation in NiGeSn-GeSn contacts. Journal of Applied Physics, 2017, 121, .	1.1	20
29	Silicon GAA NW TFET inverters with suppressed ambipolarity. , 2016, , .		2
30	Low Temperature Deposition of High-k/Metal Gate Stacks on High-Sn Content (Si)GeSn-Alloys. ACS Applied Materials & Interfaces, 2016, 8, 13133-13139.	4.0	18
31	Line Tunneling Dominating Charge Transport in SiGe/Si Heterostructure TFETs. IEEE Transactions on Electron Devices, 2016, 63, 4173-4178.	1.6	14
32	Si n-TFETs on ultra thin body with suppressed ambipolarity. , 2016, , .		0
33	Implementation of a DC compact model for double-gate Tunnel-FET based on 2D calculations and application in circuit simulation. , 2016, , .		8
34	Experimental I â€“ $V(T)$ and C â€“ V Analysis of Si Planar p-TFETs on Ultrathin Body. IEEE Transactions on Electron Devices, 2016, 63, 5036-5040.	1.6	9
35	Complementary Strained Si GAA Nanowire TFET Inverter With Suppressed Ambipolarity. IEEE Electron Device Letters, 2016, 37, 950-953.	2.2	46
36	Ion-sensitive field-effect transistor with sSi/Si0.5Ge0.5/sSOI quantum-well for high voltage sensitivity. Microelectronic Engineering, 2016, 163, 115-118.	1.1	1

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37	Experimental demonstration of strained Si nanowire GAA n-TFETs and inverter operation with complementary TFET logic at low supply voltages. Solid-State Electronics, 2016, 115, 152-159.	0.8	32
38	Strained Si nanowire GAA n-TFETs for low supply voltages. , 2015, , .		4
39	Novel SiGe/Si line tunneling TFET with high Ion at low Vdd and constant SS. , 2015, , .		38
40	Improved NiSi contacts on Si by CF4 plasma immersion ion implantation for 14nm node MOSFETs. , 2015, , .		3
41	Strained Si and SiGe Nanowire Tunnel FETs for Logic and Analog Applications. IEEE Journal of the Electron Devices Society, 2015, 3, 103-114.	1.2	70
42	Impact of TFET Unidirectionality and Ambipolarity on the Performance of 6T SRAM Cells. IEEE Journal of the Electron Devices Society, 2015, 3, 223-232.	1.2	68
43	Experimental demonstration of improved analog device performance of nanowire-TFETs. Solid-State Electronics, 2015, 113, 179-183.	0.8	9
44	Homogeneous NiSi1â^'xGex layer formation on strained SiGe with ultrathin Ni layers. Microelectronic Engineering, 2015, 139, 26-30.	1.1	2
45	High performance strained Si0.5Ge0.5 quantum-well p-MOSFETs fabricated using a high-Îº/metal-gate last process. Superlattices and Microstructures, 2015, 83, 210-215.	1.4	5
46	Ultrathin homogeneous Ni(Al) germanosilicide layer formation on strained SiGe with Al/Ni multi-layers. Microelectronic Engineering, 2015, 137, 88-91.	1.1	4
47	Experimental demonstration of planar SiGe on Si TFETs with counter doped pocket. , 2015, , .		2
48	Investigation of band-to-band tunneling parameters in sige by using MOSFET GIDL current analysis. , 2014, , .		3
49	Mobility Enhancement and Gate-Induced-Drain-Leakage Analysis of Strained-SiGe Channel p-MOSFETs with Higher-Îº LaLuO ₃ Gate Dielectric. Chinese Physics Letters, 2014, 31, 016101.	1.3	4
50	Strained silicon nanowire tunnel FETs and NAND logic. , 2014, , .		1
51	Experimental demonstration of inverter and NAND operation in p-TFET logic at ultra-low supply voltages down to V<inf>DD</inf> = 0.15 V. , 2014, , .		5
52	Experimental demonstration of improved analog device performance in GAA-NW-TFETs. , 2014, , .		8
53	Equivalent Trap Energy Level Extraction for SiGe Using Gate-Induced-Drain-Leakage Current Analysis. Chinese Physics Letters, 2014, 31, 106103.	1.3	0
54	Impact of Si cap, strain and temperature on the hole mobility of (s)Si/sSiGe/(s)SOI quantum-well p-MOSFETs. Microelectronic Engineering, 2014, 113, 5-9.	1.1	13

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55	High on-currents with highly strained Si nanowire MOSFETs. , 2014, , .		1
56	Multi-gates SOI LDMOS for improved on-state performance. , 2014, , .		0
57	Line and Point Tunneling in Scaled Si/SiGe Heterostructure TFETs. IEEE Electron Device Letters, 2014, 35, 699-701.	2.2	62
58	Ultrathin Ni silicide contacts on Si and SiGe formed with multi thin Ni/Al layers. , 2014, , .		2
59	Analysis of GeSn-SiGeSn hetero-tunnel FETs. , 2014, , .		6
60	Tunnel-FET inverters for ultra-low power logic with supply voltage down to V<inf>DD</inf> = 0.2 V. , 2014, , .		2
61	Experimental Investigation on Alloy Scattering in sSi/${m Si}_{0.5}{m Ge}_{0.5}$/sSOI Quantum-Well p-MOSFET. IEEE Transactions on Electron Devices, 2014, 61, 950-952.	1.6	5
62	Improved LDMOS performance with buried multi-finger gates. Microelectronic Engineering, 2014, 122, 29-32.	1.1	3
63	Si based tunnel FETs : Status and perspectives. , 2014, , .		1
64	Strained Si nanowire tunnel FETs and inverters. , 2013, , .		0
65	Fabrication and Characterization of Enhancement-Mode High-$kappa~{m LaLuO}_{3}$-AlGaN/GaN MIS-HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 3040-3046.	1.6	46
66	Inverters With Strained Si Nanowire Complementary Tunnel Field-Effect Transistors. IEEE Electron Device Letters, 2013, 34, 813-815.	2.2	171
67	Demonstration of improved transient response of inverters with steep slope strained Si NW TFETs by reduction of TAT with pulsed I-V and NW scaling. , 2013, , .		41
68	Gate-all-around Si nanowire array tunnelling FETs with high on-current of 75 µA/µm @ V<inf>DD</inf>=1.1V. , 2013, , .		6
69	Si based tunnel field effect transistors: Recent achievements. , 2013, , .		3
70	Low frequency noise in strained silicon nanowire array MOSFETs and Tunnel-FETs. , 2013, , .		2
71	Effects of C+ ion implantation on electrical properties of NiSiGe/SiGe contacts. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 408-411.	0.6	2
72	Ultrathin epitaxial Ni-silicide contacts on (1 0 0) Si and SiGe: Structural and electrical investigations. Microelectronic Engineering, 2013, 107, 190-195.	1.1	11

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73	Using platinum silicide as a superconductor for silicon electron coolers. , 2013, , .		1
74	Enhancement-Mode LaLuO3â€“AlGaN/GaN Metalâ€“Insulatorâ€“Semiconductor High-Electron-Mobility Transistors Using Fluorine Plasma Ion Implantation. Japanese Journal of Applied Physics, 2013, 52, 08JN02.	0.8	5
75	SiGe on SOI nanowire array TFETs with homo- and heterostructure tunnel junctions. , 2013, , .		6
76	Ultrathin highly uniform Ni(Al) germanosilicide layer with modulated B8 type Ni5(SiGe)3 phase formed on strained Si1â^'xGex layers. Applied Physics Letters, 2013, 103, .	1.5	9
77	Si based tunneling field effect transistors and inverters. , 2013, , .		0
78	Si Nanowire tunnel FETs with epitaxial NiSi<inf>2</inf> source/drain and dopant segregation. , 2012, , .		0
79	Hole Transport in Strained $hbox{Si}_{0.5} hbox{Ge}_{0.5}$ QW-MOSFETs With $langlehbox{110}angle$ and $langlehbox{100}angle$ Channel Orientations. IEEE Electron Device Letters, 2012, 33, 1105-1107.	2.2	9
80	Nanowire and planar UTB SOI Schottky Barrier MOSFETs with dopant segregation. , 2012, , .		3
81	Si tunneling transistors with high on-currents and slopes of 50 mV/dec using segregation doped Nisi<inf>2</inf> tunnel junctions. , 2012, , .		2
82	Strained silicon nanowire array MOSFETs with high-k/metal gate stack. , 2012, , .		1
83	$Omega$-Gated Silicon and Strained Silicon Nanowire Array Tunneling FETs. IEEE Electron Device Letters, 2012, 33, 1535-1537.	2.2	42
84	Tunneling field-effect transistor with a strained Si channel and a Si0.5Ge0.5 source. Solid-State Electronics, 2012, 74, 97-101.	0.8	27
85	Characteristics of higher-κ dielectric LaLuO<inf>3</inf> with TiN as gate stack. , 2012, , .		0
86	Hole Mobilities of $hbox{Si/Si}_{0.5}hbox{Ge}_{0.5}$ Quantum-Well Transistor on SOI and Strained SOI. IEEE Electron Device Letters, 2012, 33, 758-760.	2.2	15
87	Si/SiGe hetero-structure tunneling field effect transistors with in-situ doped SiGe source. , 2012, , .		4
88	AlGaN/GaN MISHEMTs With High-$kappa hbox{LaLuO}_{3}$ Gate Dielectric. IEEE Electron Device Letters, 2012, 33, 979-981.	2.2	40
89	Formation of a highly Erbium doped silicon-on-insulator layer by introducing SiOx on or into a silicon surface. Nuclear Instruments & Methods in Physics Research B, 2012, 278, 1-3.	0.6	2
90	Impact of strain and Ge concentration on the performance of planar SiGe band-to-band-tunneling transistors. Solid-State Electronics, 2012, 71, 42-47.	0.8	15

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91	Electrical characterization of Î©-gated uniaxial tensile strained Si nanowire-array metal-oxide-semiconductor field effect transistors with <100>- and <110> channel orientations. Thin Solid Films, 2012, 520, 3332-3336.	0.8	13
92	Simulation of Fabricated 20-nm Schottky Barrier MOSFETs on SOI: Impact of Barrier Lowering. IEEE Transactions on Electron Devices, 2012, 59, 1320-1327.	1.6	17
93	NiSi nano-contacts to strained and unstrained silicon nanowires. , 2011, , .		2
94	Impact of strain and Ge concentration on the performance of planar SiGe band-to-band-tunneling transistors. , 2011, , .		3
95	Tunneling field-effect transistor with a strained Si channel and a Si<inf>0.5</inf>Ge<inf>0.5</inf> source. , 2011, , .		2
96	Rare-earth oxide/TiN gate stacks on high mobility strained silicon on insulator for fully depleted metal-oxide-semiconductor field-effect transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01A903.	0.6	3
97	Lanthanum Lutetium oxide integration in a gate-first process on SOI MOSFETs. , 2011, , .		2
98	Characterization of high-Îº LaLuO3 thin film grown on AlGaN/GaN heterostructure by molecular beam deposition. Applied Physics Letters, 2011, 99, 182103.	1.5	12
99	Comparison of strained SiGe heterostructure-on-insulator (001) and (110) PMOSFETs: Câ€“V characteristics, mobility, and ON current. Solid-State Electronics, 2011, 65-66, 64-71.	0.8	4
100	Rare-Earth Scandate/TiN Gate Stacks in SOI MOSFETs Fabricated With a Full Replacement Gate Process. IEEE Transactions on Electron Devices, 2011, 58, 617-622.	1.6	9
101	High mobility compressive strained Si0.5Ge0.5 quantum well p-MOSFETs with higher-k/metal-gate. Solid-State Electronics, 2011, 62, 185-188.	0.8	19
102	20nm Gate length Schottky MOSFETs with ultra thin NiSi/epitaxial NiSi<inf>2</inf> source/drain. , 2011, , .		2
103	Epitaxial growth of Ni(Al)Si0.7Ge0.3 on Si0.7Ge0.3/Si(100) by Al interlayer mediated epitaxy. Applied Physics Letters, 2011, 98, 252101.	1.5	20
104	An Improved Si Tunnel Field Effect Transistor With a Buried Strained $hbox{Si}_{1-x}hbox{Ge}_{x}$ Source. IEEE Electron Device Letters, 2011, 32, 1480-1482.	2.2	68
105	Improved NiSi0.8Ge0.2/Si0.8Ge0.2 Contacts by C+ Pre-Implantation. Electrochemical and Solid-State Letters, 2011, 14, H261.	2.2	13
106	Electrical and Structural Properties of Ternary Rare-Earth Oxides on Si and Higher Mobility Substrates and their Integration as High-k Gate Dielectrics in MOSFET Devices. ECS Transactions, 2011, 35, 461-479.	0.3	9
107	High mobility Si-Ge channels and novel high-k materials for nanomosfets. , 2010, , .		0
108	Electrical Characterization of TbScO3/TiN Gate Stacks of MOS Capacitors and MOSFETs on Strained and Unstrained SOI. ECS Transactions, 2010, 33, 195-202.	0.3	0

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109	Formation and characterization of ultra-thin Ni silicides on strained and unstrained silicon. , 2010, , .		2
110	Formation of steep, low Schottky-barrier contacts by dopant segregation during nickel silicidation. Journal of Applied Physics, 2010, 107, 044510.	1.1	19
111	Electrical characterization of strained and unstrained silicon nanowires with nickel silicide contacts. Nanotechnology, 2010, 21, 105701.	1.3	21
112	Dislocation-Based Si-Nanodevices. Japanese Journal of Applied Physics, 2010, 49, 04DJ02.	0.8	26
113	Non-linear analysis of n-type Schottky-Barrier MOSFETs. , 2010, , .		0
114	Ultrathin Ni Silicides With Low Contact Resistance on Strained and Unstrained Silicon. IEEE Electron Device Letters, 2010, 31, 350-352.	2.2	57
115	MOSFETs with high mobility channel materials and higher-k/metal gate stack. , 2010, , .		4
116	Radio-Frequency Study of Dopant-Segregated n-Type SB-MOSFETs on Thin-Body SOI. IEEE Electron Device Letters, 2010, 31, 537-539.	2.2	23
117	Interfacial and electrical characterization of HfO<inf>2</inf> gate dielectric film with a blocking layer of Al<inf>2</inf>O<inf>3</inf>. , 2009, , .		0
118	Measurement of effective electron mass in biaxial tensile strained silicon on insulator. Applied Physics Letters, 2009, 95, .	1.5	25
119	Epitaxial growth of NiSi2 induced by sulfur segregationat the NiSi2/Si(100) interface. Journal of Materials Research, 2009, 24, 135-139.	1.2	2
120	NiSi2/Si interface chemistry and epitaxial growth mode. Acta Materialia, 2009, 57, 232-236.	3.8	19
121	High performance Schottky barrier MOSFETs on UTB SOI. , 2009, , .		3
122	Performance enhancement of uniaxially-tensile strained Si NW-nFETs fabricated by lateral strain relaxation of SSOI. , 2009, , .		3
123	Schottky barrier height modulation by Arsenic Dopant segregation. , 2008, , .		7
124	Nickel silicidation on sulfur implanted Si(100). , 2008, , .		0
125	Schottky-barrier height tuning of Ni and Pt germanide/n-Ge contacts using dopant segregation. , 2008, , .		5
126	Strained Silicon on Wafer Level by Waferbonding: Materials Processing, Strain Measurements and Strain Relaxation. ECS Transactions, 2008, 16, 311-320.	0.3	8

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127	Segregation of ion implanted sulfur in Si(100) after annealing and nickel silicidation. Journal of Applied Physics, 2007, 102, .	1.1	15
128	Large current enhancement in n-MOSFETs with strained Si on insulator. , 2007, , .		1
129	Thermal stability of CoSi2layers implemented in a silicon-on-insulator substrate. Semiconductor Science and Technology, 2006, 21, 157-161.	1.0	4
130	Schottky-barrier height tuning using dopant segregation in Schottky-barrier MOSFETs on fully-depleted SOI. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	2
131	Effective Schottky barrier lowering in silicon-on-insulator Schottky-barrier metal-oxide-semiconductor field-effect transistors using dopant segregation. Applied Physics Letters, 2005, 87, 263505.	1.5	81
132	Tuning of NiSiâˆ•Si Schottky barrier heights by sulfur segregation during Ni silicidation. Applied Physics Letters, 2005, 86, 062108.	1.5	127
133	Nanopatterning of epitaxial CoSi2 using oxidation in a local stress field and fabrication of nanometer metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2004, 96, 5775-5780.	1.1	5
134	Full silicidation process for making CoSi2 on SiO2. Applied Physics Letters, 2004, 84, 3292-3294.	1.5	8
135	Fabrication of Schottky barrier MOSFETs on SOI by a self-assembly CoSi2-patterning method. Solid-State Electronics, 2003, 47, 1183-1186.	0.8	16
136	Fabrication of Schottky barrier MOSFETs using self-assembly CoSi2 nanopatterning and spacer gate technologies. Microelectronic Engineering, 2003, 70, 186-190.	1.1	6
137	Self-assembly patterning of epitaxial CoSi2 nano-structures. Microelectronic Engineering, 2002, 64, 443-447.	1.1	4
138	Self-Assembly CoSi2-Nanostructures for Fabrication of Schottky Barrier MOSFETs on SOI. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
139	Fabrication of epitaxial CoSi2 nanowires. Applied Physics Letters, 2001, 79, 824-826.	1.5	18
140	Properties of ion implanted epitaxial CoSi2/Si(1 0 0) after rapid thermal oxidation. Nuclear Instruments & Methods in Physics Research B, 2000, 164-165, 1004-1009.	0.6	0
141	Nanometer patterning of epitaxial CoSi2/Si(100) for ultrashort channel Schottky barrier metalâ€“oxideâ€“semiconductor field effect transistors. Applied Physics Letters, 1999, 74, 454-456.	1.5	37
142	Nanometer patterning of epitaxial CoSi2/Si(100) by local oxidation. Solid-State Electronics, 1999, 43, 1091-1094.	0.8	1
143	Epitaxial growth and electrical transport properties of La0.5Sr0.5Co03 thin films prepared by pulsed laser deposition. Science in China Series A: Mathematics, 1999, 42, 865-872.	0.5	3
144	Fabrication of nanometer Schottky-tunneling MOSFETs by a novel silicide nanopatterning method. , 1999, , .		0

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145	Effects of MeV Si ion irradiation on the properties of shallow P+N junctions. Nuclear Instruments & Methods in Physics Research B, 1998, 135, 280-284.	0.6	2
146	Structural characteristics and the control of crystallographic orientation of CeO2 thin films prepared by laser ablation. Nuclear Instruments & Methods in Physics Research B, 1998, 135, 535-539.	0.6	8
147	Influences of substrates and substrate temperatures on characteristics of epitaxial La0.5Sr0.5CoO3 thin films. Thin Solid Films, 1998, 323, 304-308.	0.8	23
148	Growth, Patterning and Microelectronic Applications of Epitaxial Cobaltdisilicide. Materials Research Society Symposia Proceedings, 1998, 514, 145.	0.1	4
149	Growth of ferroelectric (K0.5Na0.5)0.2(Sr0.75Ba0.25)0.9Nb2O6 thin films by fulsed laser deposition. Solid State Communications, 1997, 103, 285-289.	0.9	5
150	Reduction of secondary defects in 50 keV P+-implanted Si(100) by MeV Si ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1996, 108, 81-84.	0.6	4
151	Ion beam defect engineering in semiconductors and optoelectric materials. Nuclear Instruments & Methods in Physics Research B, 1996, 115, 421-429.	0.6	4
152	Longitudinal and transverse moments of the distribution of MeV Ti ions implanted in Si measured by SIMS. Journal Physics D: Applied Physics, 1995, 28, 1158-1161.	1.3	4
153	Ion-beam-induced solid phase crystallization of MeV Si ⁺ -implanted Si(100). Acta Physica Sinica (overseas Edition), 1995, 4, 118-124.	0.1	1
154	Dechannelling analysis of damage in Si created by MeV Ti ions. Journal Physics D: Applied Physics, 1994, 27, 571-573.	1.3	0
155	Damage behavior of silicon by MeV Ge+ irradiation under tilted angle. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3027.	1.6	0
156	Range profiles of implanted argon ions in polymers. Radiation Effects and Defects in Solids, 1994, 128, 287-293.	0.4	2
157	Channeling study on damage in potassium titanyl phosphate induced by ion irradiation. Physical Review B, 1994, 50, 770-776.	1.1	3
158	Investigation of depth distributions of defects in Si created by high energy Ti ions. Vacuum, 1994, 45, 955-958.	1.6	0
159	RBS studies of the lattice damage caused by 1 Me V Si+ implantation into Al0.3Ga0.7As/GaAs superlattices at elevated temperature. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 392-395.	0.6	1
160	Damage accumulation and amorphization in GaAs by MeV Si+ ion implantation at different tilt angles. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 415-418.	0.6	4
161	Two-dimensional distributions of Xe ions implanted in Si3N4 films. Vacuum, 1993, 44, 1045-1048.	1.6	0
162	Damage formation in Si(100) induced by MeV self-ion implantation. Nuclear Instruments & Methods in Physics Research B, 1993, 82, 575-578.	0.6	5

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163	Lattice disorder in silicon induced by 2.0 MeV Cu+ irradiation. Applied Physics A: Solids and Surfaces, 1992, 55, 332-334.	1.4	2
164	Damage profiles in silicon induced by 1.0 MeV Ti ions at tilted angle incidence. Physics Letters, Section A: General, Atomic and Solid State Physics, 1992, 166, 361-364.	0.9	0
165	Range profiles of xenon in PVA. Nuclear Instruments & Methods in Physics Research B, 1990, 47, 351-354.	0.6	2
166	Lateral straggling of Hg+ in both amorphized quartz crystal and Ni film by RBS. Physics Letters, Section A: General, Atomic and Solid State Physics, 1990, 150, 277-280.	0.9	3
167	Range profiles of Xe ions at energies from 50 to 400 keV in potassium titanyl phosphate. Physics Letters, Section A: General, Atomic and Solid State Physics, 1990, 151, 241-245.	0.9	3
168	Reduction of secondary defects and diffusion of B atoms in BF/sub 2/-implanted Si(100) by ion-beam defect engineering. , 0, , .		0
169	Schottky barrier height modulation using dopant segregation in schottky-barrier SOI-MOSFETs. , 0, , .		37